(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
12 August 2004 (12.08.2004)

PCT

(10) International Publication Number
WO 2004/068576 A2

(51) International Patent Classification[7]: H01L 21/768

(21) International Application Number:
PCT/US2003/041185

(22) International Filing Date:
22 December 2003 (22.12.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
103 02 644.4 23 January 2003 (23.01.2003) DE
10/602,192 24 June 2003 (24.06.2003) US

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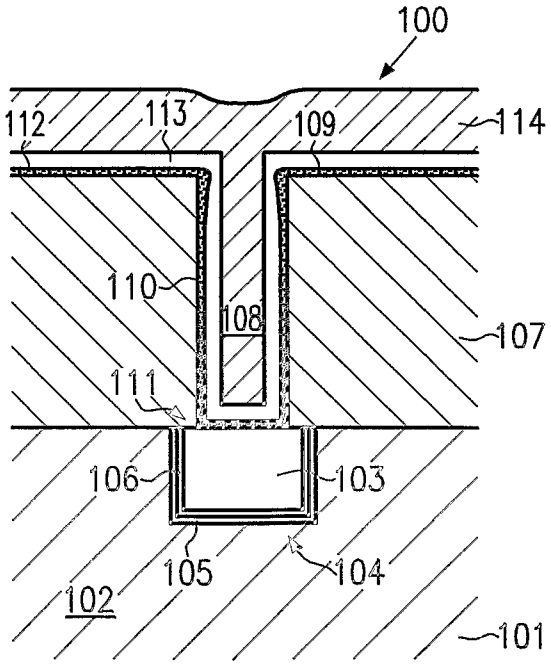
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(regional)*: ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *without international search report and to be republished upon receipt of that report*

[Continued on next page]

(54) Title: METHOD OF FORMING A CATALYST CONTAINING LAYER OVER A PATTERNED DIELECTRIC



(57) Abstract: A metal layer is maybe formed by means of a plating process on a surface region of an underlying material catalytically activated in that a catalyst is deposited or incorporated by CVD, PVD or ALD at least partially during the deposition of the underlying material. In this way, superior metal seed layers may be formed in high aspect ratio vias of metallization structures.

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